ON Semiconductor®

FDS8817NZ

## N-Channel PowerTrench® MOSFET
30V, 15A, 7.0mΩ

Features

- Max $r_{DS(on)}$ = 7mΩ at V_{GS} = 10V, I_D = 15A
- Max $r_{DS(on)}$ = 10mΩ at V_{GS} = 4.5V, I_D = 12.6A
- HBM ESD protection level of 3.8KV typical (note 3)
- High performance trench technology for extremely low $r_{DS(on)}$
- High power and current handling capability
- RoHS compliant

General Description

This N-Channel MOSFET is produced using ON Semiconductor's advanced PowerTrench® process that has been especially tailored to minimize the on-state resistance.

This device is well suited for Power Management and load switching applications common in Notebook Computers and Portable Battery Packs.

SO-8

Pin 1
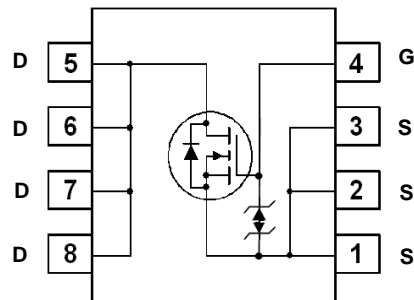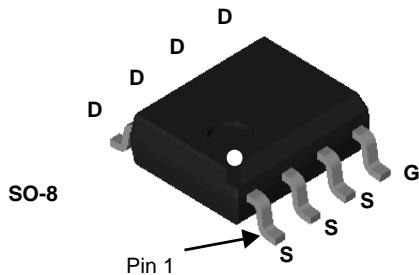
MOSFET Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V_{DS}	Drain to Source Voltage		30	V
V_{GS}	Gate to Source Voltage		±20	V
I_D	Drain Current -Continuous	(Note 1a)	15	A
	-Pulsed		60	
E_{AS}	Single Pulse Avalanche Energy	(Note 4)	181	mJ
P_D	Power Dissipation	(Note 1a)	2.5	W
	Power Dissipation	(Note 1b)	1.0	
T_J, T_{STG}	Operating and Storage Junction Temperature Range		-55 to +150	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	(Note 1)	25	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	50	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1b)	125	

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape Width	Quantity
FDS8817NZ	FDS8817NZ	13"	12mm	2500 units

Electrical Characteristics $T_J = 25°C$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250\mu A$, $V_{GS} = 0V$	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu A$, referenced to 25°C		20		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 24V$, $V_{GS} = 0V$			1	μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm20V$, $V_{DS} = 0V$			±10	μA
On Characteristics (Note 2)						
$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250\mu A$	1	1.8	3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\mu A$, referenced to 25°C		−6		mV/°C
$r_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10V$, $I_D = 15A$		5.4	7	mΩ
		$V_{GS} = 4.5V$, $I_D = 12.6A$		7.0	10	
		$V_{GS} = 10V$, $I_D = 15A$ $T_J = 125°C$		7.5	11	
g_{FS}	Forward Transconductance	$V_{DS} = 5V$, $I_D = 15A$		54		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS} = 15V$, $V_{GS} = 0V$, f = 1MHz		1805	2400	pF
C_{oss}	Output Capacitance			335	445	pF
C_{rss}	Reverse Transfer Capacitance			200	300	pF
R_g	Gate Resistance	f = 1MHz		1.4		Ω
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 15V$, $I_D = 15A$ $V_{GS} = 10V$, $R_{GEN} = 6\Omega$		11	22	ns
t_r	Rise Time			13	26	ns
$t_{d(off)}$	Turn-Off Delay Time			25	40	ns
t_f	Fall Time			7	14	ns
Q_g	Total Gate Charge	$V_{GS} = 0V$ to 10V $V_{DD} = 15V$		32	45	nC
Q_g	Total Gate Charge	$V_{GS} = 0V$ to 5V $I_D = 15A$		17	24	nC
Q_{gs}	Gate to Source Charge			6		nC
Q_{gd}	Gate to Drain "Miller" Charge			7		nC
Drain-Source Diode Characteristics						
V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0V$, $I_S = 2.1A$ (Note 2)		0.8	1.2	V
t_{rr}	Reverse Recovery Time	$I_F = 15A$, di/dt = 100A/μs		24	36	ns
Q_{rr}	Reverse Recovery Charge			15	23	nC

Notes:
1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to- ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta JA}$ is determined by the user's board design.

a) 50°C/W when mounted on a 1in² pad of 2 oz copper.

b) 125°C/W when mounted on a minimum pad .

2. Pulse Test: Pulse Width < 300 us, Duty Cycle < 2%.
3. The diode connected between the gate and source serves only as protection against ESD . No gate overvoltage rating is implied.
4. Starting $T_J = 25°C$, L = 3mH, $I_{AS} = 11A$, $V_{DD} = 30V$, $V_{GS} = 10V$.

Typical Characteristics $T_J = 25°C$ unless otherwise noted
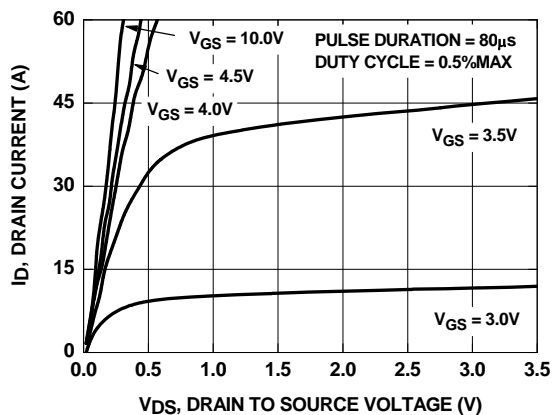

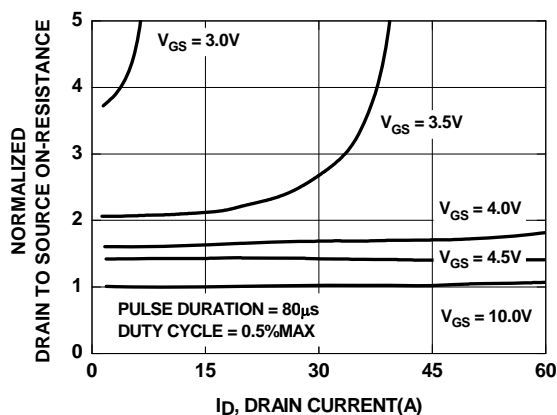**Figure 1. On-Region Characteristics**

Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage
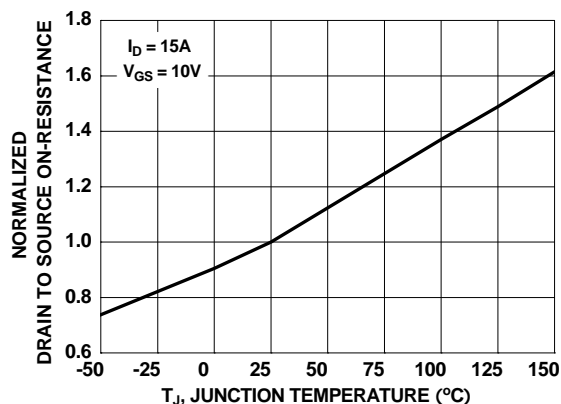

Figure 3. Normalized On-Resistance vs Junction Temperature
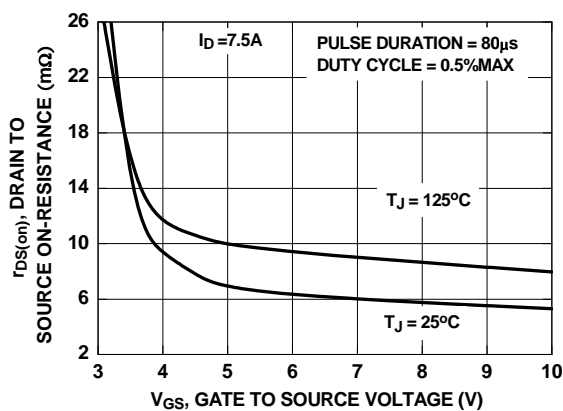

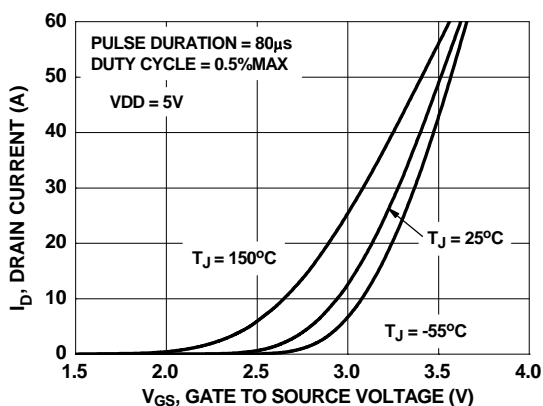**Figure 4. On-Resistance vs Gate to Source Voltage**

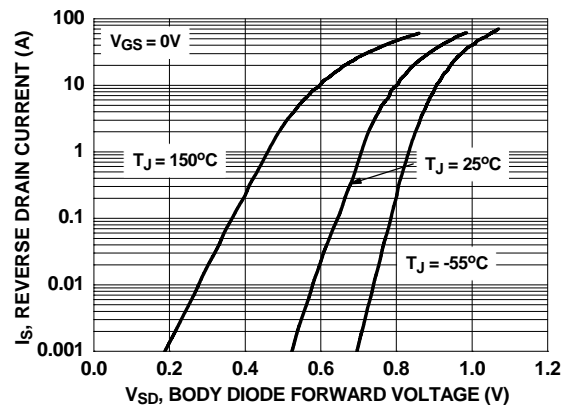**Figure 5. Transfer Characteristics**

Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics T_J = 25°C unless otherwise noted
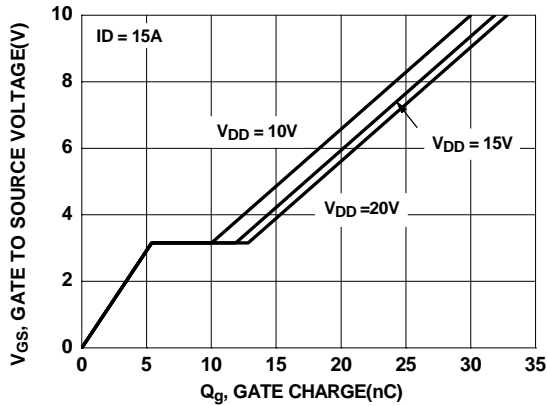
Figure 7. Gate Charge Characteristics
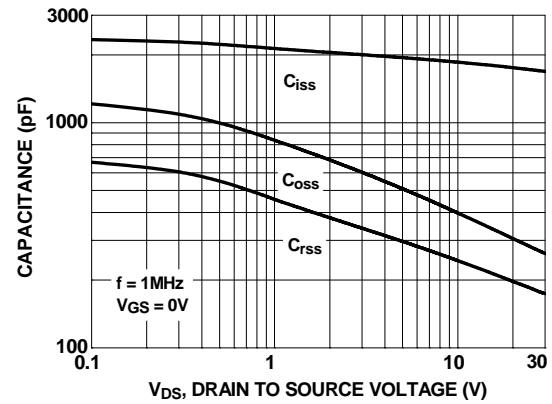
Figure 8. Capacitance vs Drain to Source Voltage
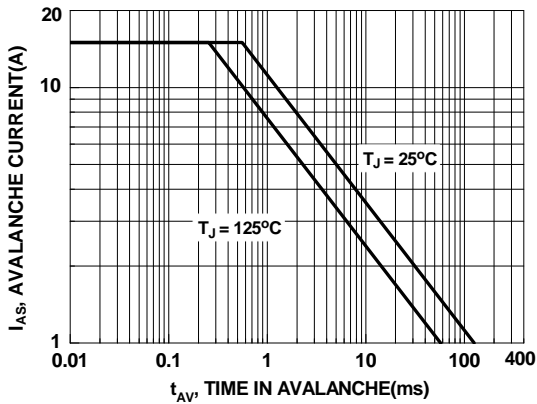
Figure 9. Unclamped Inductive Switching Capability
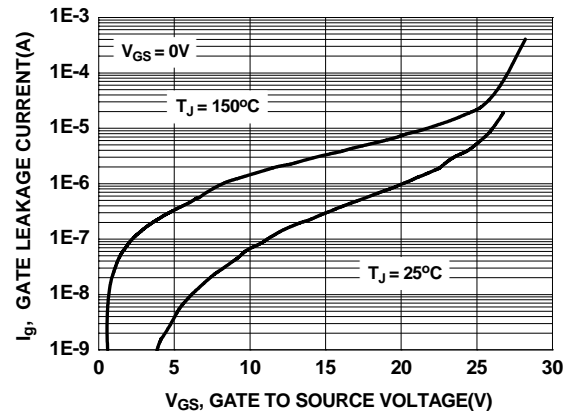
Figure 10. Gate Leakage Current vs Gate to Source Voltage
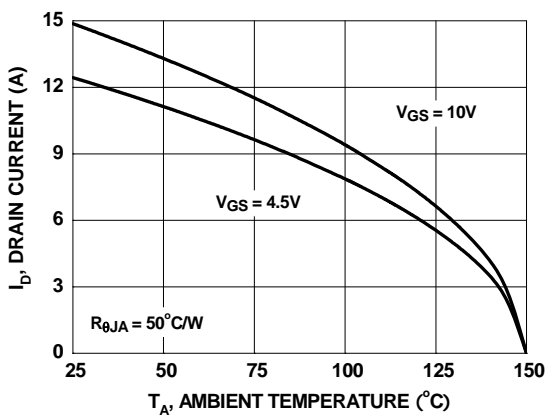
Figure 11. Maximum Continuous Drain Current vs Ambient Temperature
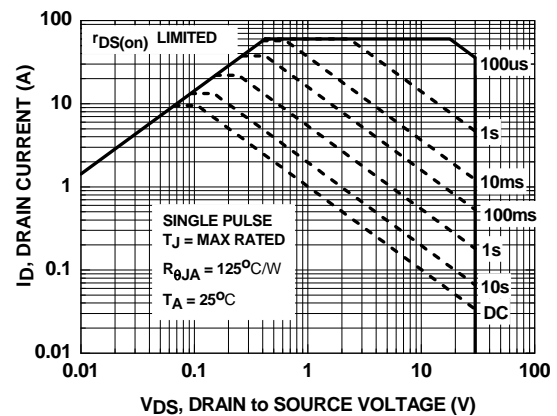
Figure 12. Forward Bias Safe Operating Area

Typical Characteristics T_J = 25°C unless otherwise noted

FOR TEMPERATURES
ABOVE 25°C DERATE PEAK
CURRENT AS FOLLOWS:

$$I = I_{25} \left[\sqrt{\frac{150 - T_A}{125}} \right]$$

T_A = 25°C

V_GS = 10V

SINGLE PULSE
$R_{\theta JA}$ = 125°C/W

NORMALIZED THERMAL IMPEDANCE, $Z_{\theta JA}$

t, RECTANGULAR PULSE DURATION (s)
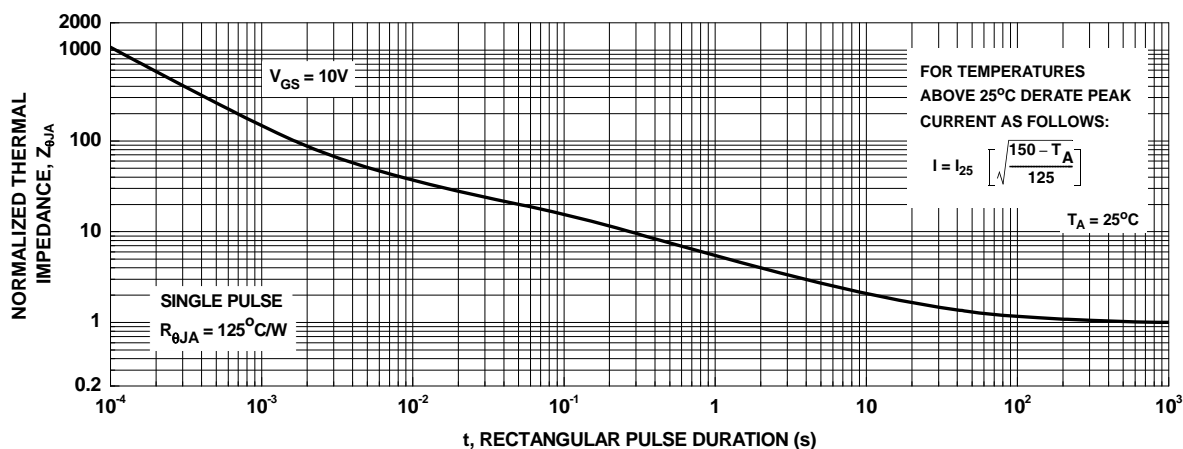
Figure 13. Single Pulse Maximum Power Dissipation

DUTY CYCLE-DESCENDING ORDER

D = 0.5
0.2
0.1
0.05
0.02
0.01

SINGLE PULSE
$R_{\theta JA}$ = 125°C/W

NORMALIZED THERMAL IMPEDANCE, $Z_{\theta JA}$

t, RECTANGULAR PULSE DURATION (s)

P_{DM}

t_1

t_2

NOES:
DUTY FACTOR: D = t_1/t_2
PEAK T_J = P_{DM} x $Z_{\theta JA}$ x $R_{\theta JA}$ + T_A
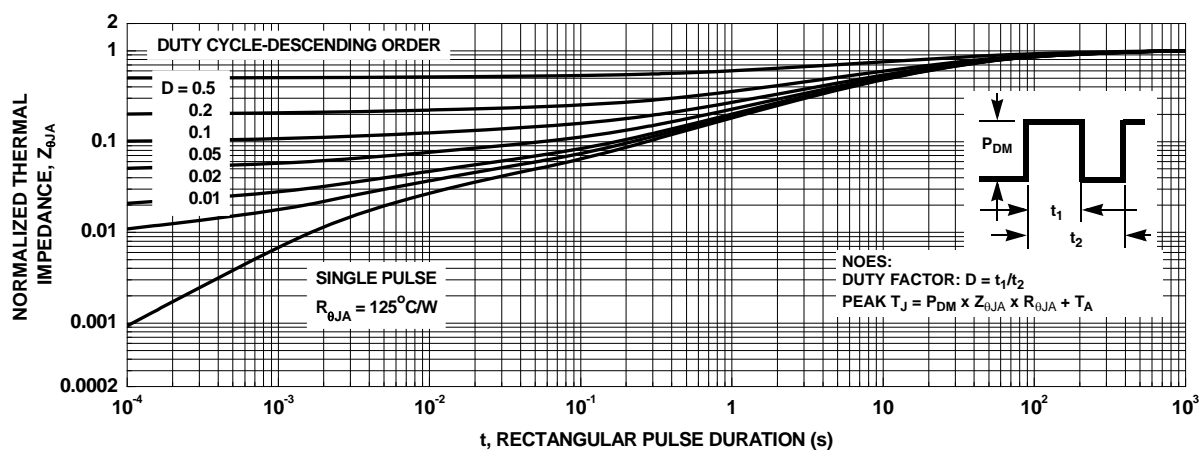
Figure 14. Transient Thermal Response Curve

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